

[MoB3] Optical Characterization

Session Date	July 13 (Mon.), 2026
Session Time	16:05–17:50
Session Room	Room B (Baekrok Hall B, 1F)
Session Chairs	Prof. Tetsuya Takeuchi (Meijo University, Japan), Dr. Frank Brunner (Ferdinand-Braun-Institute, Germany)

[MoB3–1] [Invited]

16:05–16:35

Optical In-Situ Metrology and MOVPE: Versatile Toolbox for Laser Device Growth

A. Maaßdorf, M. Brendel, S. Breuer, and M. Weyers, Ferdinand-Braun-Institut, Germany

[MoB3–2]

16:35–16:50

Composition-Dependent Raman Anisotropy in MOVPE-Grown Non-Polar (11-20) $\text{Al}_x\text{Ga}_{1-x}\text{N}$

A Azizur Rahman¹, Eeshika Suresh^{1,2}, Maheshwar Gokhale¹, Amit P Shah¹, Kailash Rustagi¹, and Arnab Bhattacharya¹, ¹Tata Institute of Fundamental Research, India, ²Amrita Vishwa Vidyapeetham, India

[MoB3–3]

16:50–17:05

Optical Response and Anisotropy in MOVPE-Grown Non-Polar $\text{Al}_x\text{Ga}_{1-x}\text{N}$: Insights from Mueller Matrix Ellipsometry

A Azizur Rahman¹, Sanchali Datta^{1,2}, Maheshwar Gokhale¹, Amit P Shah¹, and Arnab Bhattacharya¹, ¹Tata Institute of Fundamental Research, India, ²Tripura University, India

[MoB3–4]

17:05–17:20

WITHDRAWN

[MoB3–5]

17:20–17:35

Temperature- and Wavelength-Dependent Photoluminescence Lifetimes in InGaN Quantum Wells with Varying Indium Compositions

Ririka Yamagata¹, Soma Hatanaka¹, Soya Yamagishi¹, Itsuki Shimbo¹, Atsushi A. Yamaguchi¹, Kazunori Iwamitsu², and Shigetaka Tomiya², ¹Kanazawa Institute of Technology, Japan, ²Nara Institute of Science and Technology, Japan

Functional-Form Analysis of Photoluminescence Decay in InGaN Quantum Wells

Arata Suzuki¹, Ririka Yamagata¹, Itsuki Shimbo¹, Atsushi A. Yamaguchi¹, Daisuke Iida², and Kazuhiro Ohkawa², ¹Kanazawa Institute of Technology, Japan, ²King Abdullah University of Science and Technology, Saudi Arabia